### MAX14483

# 6-Channel, Low-Power, 3.75kV<sub>RMS</sub>, SPI Digital Isolator

### **General Description**

The MAX14483 is a 6-channel, 3.75kV<sub>RMS</sub> digital galvanic isolator using Maxim's proprietary process technology. The six signal channels are individually optimized for SPI applications and include very low propagation delay on the SDI, SDO, and SCLK channels. The SDO channel's tri-state control is enabled by the CS input as well as a second enable control input pin (SDOEN), allowing a single MAX14483 to isolate multiple SPI devices. To simplify system design, an open-drain FAULT output can be wire ORed with error outputs from other devices. In addition, an auxiliary channel (AUX) is available for passing timing or control signals from the master side to the slave side and power monitors (SAA, SBA) are provided for both power domains to signal if the opposite side of the isolator is ready for operation. Independent 1.71V to 5.5V supplies on each side of the isolator also make the device suitable for use as a level translator.

The MAX14483 has an isolation rating of  $3.75 \mathrm{kV}_{RMS}$  for 60 seconds and is available in a 20-pin SSOP package with 5.5mm of creepage and clearance. The package material has a minimum comparative tracking index (CTI) of 400V, which gives it a group II rating in creepage tables.

The MAX14483 is rated for operation at ambient temperatures of  $-40^{\circ}$ C to  $+125^{\circ}$ C.

# **Applications**

- Programmable Logic Controllers
- Industrial Automation
- Process Automation
- Building Automation
- Robotics
- General SPI-bus Isolation

### **Benefits and Features**

- Saves Space and Components
  - · 6 Isolated Channels in a 20-SSOP Package
- Low Propagation Delay on SCLK, SDI, and SDO
  - Up to 100MHz Clock, 200Mbps Data Rate
  - · 10ns Typical Propagation Delay
  - · 2ns Maximum Pulse Width Distortion
  - · 250ps Typical Peak Jitter
- Robust Galvanic Isolation of Digital Signals
  - Withstands 3.75kV<sub>RMS</sub> for 60s (V<sub>ISO</sub>)
  - Continuously Withstands 450V<sub>RMS</sub> (V<sub>IOWM</sub>)
  - Withstands ±10kV Surge between GNDA and GNDB with 1.2/50µs Waveform
  - High CMTI (50kV/µs, Typical)
- Flexible System Design
  - Wide 1.71V to 5.5V Voltage Range on Each Side
  - SDOEN Control Pin for Sharing Isolators
  - Open-Drain FAULT Channel for Shared Interrupt on Master Side
  - · Auxiliary Channel for Timing or Control
- Low Power Consumption
  - 1.53mW per Channel at SCLK = 10MHz with V<sub>DD</sub> = 3.3V
  - 0.77mW per Channel at SCLK = 10MHz with V<sub>DD</sub> = 1.8V

# **Safety Regulatory Approvals**

- UL According to UL1577
- cUL According to CSA Bulletin 5A

<u>Ordering Information</u> and <u>Typical Operating Circuits</u> appear at end of data sheet.



## **Absolute Maximum Ratings**

V <sub>DDA</sub> to GNDA, V <sub>DDB</sub> to GNDB0.3V to +6V	Short Circuit Continuous Current (OFAULT) 100mA
ĪCS, ISCLK, ISDI, IAUX, SDOEN, OFAULT	Continuous Power Dissipation
to GNDB0.3V to +6V	Single Layer Board T <sub>A</sub> = +70°C640mW
OSDO, SAA to GNDB0.3V to (V <sub>DDB</sub> + 0.3V)	Derate above +70°C8mW/°C
ISDO, IFAULT, IRDY to GNDA0.3V to +6V	Multilayer Board T <sub>A</sub> = +70°C964mW
OCS, OSCLK, OSDI, OAUX, SBA	Derate above +70°C12mW/°C
to GNDA0.3V to (V <sub>DDA</sub> + 0.3V)	Operating Temperature Range40°C to +125°C
Short-Circuit Duration	Maximum Junction Temperature+150°C
OCS, OSCLK, OSDI, OAUX, SBA to V <sub>DDA</sub>	Storage Temperature Range60°C to +150°C
or GNDAContinuous	Soldering Temperature (reflow)+260°C
OSDO, SAA to V <sub>DDB</sub> or GNDBContinuous	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **Package Information**

PACKAGE TYPE: 20 SSOP	PACKAGE TYPE: 20 SSOP					
Package Code	A20MS+7					
Outline Number	<u>21-0056</u>					
Land Pattern Number	90-0094					
THERMAL RESISTANCE, SINGLE-LAYER BOA	RD					
Junction to Ambient (θ <sub>JA</sub> )	125°C/W					
Junction to Case $(\theta_{JC})$	33°C/W					
THERMAL RESISTANCE, FOUR-LAYER BOAR	D					
Junction to Ambient (θ <sub>JA</sub> )	83°C/W					
Junction to Case (θ <sub>JC</sub> )	33°C/W					

For the latest package outline information and land patterns (footprints), go to <a href="www.maximintegrated.com/packages">www.maximintegrated.com/packages</a>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

### **DC Electrical Characteristics**

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, T_{A} = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted.}$  Typical values are at  $V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_{A} = +25^{\circ}\text{C}, \text{ unless otherwise noted.}$  (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLY						
Supply Voltage	$V_{DDA}$	Relative to GNDA	1.71		5.5	V
	$V_{DDB}$	Relative to GNDB	1.71		5.5	V
Undervoltage-Lockout Threshold	V <sub>UVLO</sub> _	V <sub>DD</sub> _rising	1.5	1.6	1.66	V
Undervoltage-Lockout Threshold Hysteresis	V <sub>UVLO_HYST</sub>			45		mV

# **DC Electrical Characteristics (continued)**

 $(V_{DDA} - V_{GNDA} = 1.71 \text{V to } 5.5 \text{V}, V_{DDB} - V_{GNDB} = 1.71 \text{V to } 5.5 \text{V}, T_{A} = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = 3.3 \text{V}, V_{DDB} - V_{GNDB} = 3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_{A} = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Note 1)}$ 

PARAMETER	SYMBOL	CONDITIO	NS	MIN	TYP	MAX	UNITS
		IRDY = 0V, SDOEN =	V <sub>DDA</sub> = 5V		1.07	1.86	
		0V, all other inputs =	V <sub>DDA</sub> = 3.3V		1.04	1.81	
		500kHz square wave,	V <sub>DDA</sub> = 2.5V		1.03	1.79	
Supply Current Side A		$C_L = 0pF$	V <sub>DDA</sub> = 1.8V		1.00	1.59	
(Note 2)	$I_{DDA}$	10MHz square wave	V <sub>DDA</sub> = 5V		1.71	2.59	mA
		on ISCLK, 5MHz	V <sub>DDA</sub> = 3.3V		1.46	2.32	
		square wave on ISDO and ISDI, all other	V <sub>DDA</sub> = 2.5V		1.39	2.21	
		inputs = 0V, C <sub>L</sub> = 0pF	V <sub>DDA</sub> = 1.8V		1.30	1.94	
		IRDY = 0V, SDOEN =	V <sub>DDB</sub> = 5V		0.92	1.64	
		0V, all other inputs =	V <sub>DDB</sub> = 3.3V		0.90	1.59	
		500kHz square wave,	V <sub>DDB</sub> = 2.5V		0.88	1.57	
Supply Current Side B	I	$C_L = 0pF$	V <sub>DDB</sub> = 1.8V		0.86	1.27	
(Note 2)	I <sub>DDB</sub>	10MHz square wave on ISCLK, 5MHz square wave on ISDO and ISDI, all other	V <sub>DDB</sub> = 5V		1.46	2.30	mA
			V <sub>DDB</sub> = 3.3V		1.33	2.18	
			V <sub>DDB</sub> = 2.5V		1.33	2.14	
		inputs = 0V, C <sub>L</sub> = 0pF			1.28	1.80	
LOGIC INPUTS AND OUTPUTS							
		2.25V ≤ V <sub>DD</sub> _ ≤ 5.5V		0.7 x V <sub>DD</sub> _			
Input High Voltage	$V_{IH}$	1.71V ≤ V <sub>DD</sub> _ < 2.25V		0.75 x V <sub>DD</sub> _			V
	.,	2.25V ≤ V <sub>DD</sub> ≤ 5.5V				0.8	,,
Input Low Voltage	$V_{IL}$	1.71V ≤ V <sub>DD</sub> < 2.25V				0.7	V
Input Hysteresis	V <sub>HYS</sub>				410		mV
Input Pullup Current (Note 3)	I <sub>PU</sub>	IAUX, ICS, SDOEN, IRI	DΥ	-10	-5	-1.5	μΑ
Input Pulldown Current (Note 3)	I <sub>PD</sub>	ĪFAULT, ISDO, ISDI, IS	CLK	1.5	5	10	μΑ
Input Capacitance	C <sub>IN</sub>	f <sub>SW</sub> = 1MHz			2		pF
Output Voltage High (Note 3)	V <sub>OH</sub>	V <sub>O</sub> _relative to GND_ I <sub>O</sub> _ = 4mA source		V <sub>DD</sub> 0.4			V
Output Voltage Low (Note 3)	V <sub>OL</sub>	V <sub>O</sub> _relative to GND_ I <sub>O</sub> _ = 4mA sink				0.4	V
Output High-Impedance Leakage Current (Note 3)	I <sub>OL</sub>	OSDO, OFAULT		-1		1	μΑ

# **Dynamic Characteristics**

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_{L}=15pF,~T_{A}=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_{A}=+25^{\circ}C,~unless~otherwise~noted.)~(Note~2)$ 

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
LOW DATA RATE CHANNELS	6 - IFAULT, OF	AULT, IAUX, OA	AUX, ĪCS, ŌCS				
Common-Mode Transient Immunity	CMTI	I_ = GND_ or \	/ <sub>DD_</sub> (Note 4)		50		kV/μs
Maximum Data Rate	DR <sub>MAX</sub>			25			Mbps
Minimum Pulse Width	PW <sub>MIN</sub>	I_ to O_				40	ns
Glitch Rejection		I_ to O_		10	17	29	ns
			$4.5V \le V_{DD} \le 5.5V$	17.4	23.9	32.5	
		I_ to O_,	$3.0V \le V_{DD} \le 3.6V$	17.6	24.4	33.7	
	t <sub>PLH</sub>	C <sub>L</sub> = 15pF	$2.25V \le V_{DD} \le 2.75V$	18.3	25.8	36.7	ns
Propagation Delay (Figure 1)	PLH		$1.71V \le V_{DD} \le 1.89V$	20.7	29.6	43.5	
		IFAULT to OFAULT	Open drain output, R <sub>pullup</sub> = 10kΩ, C <sub>L</sub> = 15pF		150		
		I_ to O_, C <sub>L</sub> = 15pF	4.5V ≤ V <sub>DD</sub> ≤ 5.5V	16.9	23.4	33.6	ns
			$3.0V \le V_{DD} \le 3.6V$	17.2	24.2	35.1	
	<sup>1</sup> PHL		$2.25V \le V_{DD} \le 2.75V$	17.8	25.4	38.2	
			1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V	19.8	29.3	45.8	1
Pulse Width Distortion	PWD	t <sub>PLH</sub> - t <sub>PHL</sub>			0.4	4	ns
		4.5V ≤ V <sub>DD</sub> _ ≤	5.5V			15.1	
	t	3.0V ≤ V <sub>DD</sub> _ ≤	3.6V			15	
	t <sub>SPLH</sub>	2.25V ≤ V <sub>DD</sub> _:	≤ 2.75V			15.4	
Propagation Delay Skew		1.71V ≤ V <sub>DD</sub> ≤ 1.89V				20.5	ne
Part-to-Part (Same Channel)		4.5V ≤ V <sub>DD</sub> _ ≤	5.5V			13.9	ns
	<b>+</b>	3.0V ≤ V <sub>DD</sub> _ ≤	3.6V			14.2	
	tsphl	2.25V ≤ V <sub>DD</sub> _ ≤ 2.75V				16	
		1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V				21.8	
Propagation Delay Skew Channel-to-Channel	t <sub>SCSLH</sub>	1.71V ≤ V <sub>DD</sub> _:	≤ 5.5V			2	ns
(Same Direction)	tscshl	1.71V ≤ V <sub>DD</sub> _ ≤ 5.5V				2	115

# **Dynamic Characteristics (continued)**

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_L=15pF,~T_A=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_A=+25^{\circ}C,~unless~otherwise~noted.)~(Note~2)$ 

PARAMETER	SYMBOL	C	CONDITIONS	MIN	TYP	MAX	UNITS
		4.5V ≤ V <sub>DD</sub> ≤	5.5V			13.9	
	_	3.0V ≤ V <sub>DD</sub> ≤			13.7		
	tscolh	2.25V ≤ V <sub>DD</sub> _ ≤	≤ 2.75V			14.2	]
Propagation Delay Skew Channel-to-Channel (Opposite Direction)		1.71V ≤ V <sub>DD</sub> ≤	≤ 1.89V			19.4	1
		4.5V ≤ V <sub>DD</sub> ≤	5.5V			13	ns
(Opposito Bilocatori)		3.0V ≤ V <sub>DD</sub> _ ≤	3.6V			12.9	1
	tscohl	2.25V ≤ V <sub>DD</sub> ≤				14.4	1
		1.71V ≤ V <sub>DD</sub> ≤	≤ 1.89V			20.1	1
Peak Eye Diagram Jitter	T <sub>JIT(PK)</sub>	25Mbps			250		ps
		4.5V ≤ V <sub>DD</sub> ≤	5.5V			1.6	
D: T: (F: 4)		3.0V ≤ V <sub>DD</sub> ≤	3.6V			2.2	1
Rise Time (Figure 1)	t <sub>R</sub>	2.25V ≤ V <sub>DD</sub> ≤	≤ 2.75V			3	ns
		1.71V ≤ V <sub>DD</sub> ≤ 1.89V				4.5	ı
		4.5V ≤ V <sub>DD</sub> ≤ 5.5V				1.4	
		3.0V ≤ V <sub>DD</sub> ≤ 3.6V				2	ns
Fall Time ( <u>Figure 1</u> )	t <sub>F</sub>	2.25V ≤ V <sub>DD</sub> ≤ 2.75V			,	2.8	
		1.71V ≤ V <sub>DD</sub> ≤ 1.89V			,	5.1	
SPI DATA RATE CHANNELS	s - ISDI, OSDI, I	SDO, OSDO, IS	CLK, OSCLK				,
Common-Mode Transient Immunity	СМТІ	I_ = GND_ or V	' <sub>DD_</sub> (Note 4)		50		kV/μs
		2.25V ≤ V <sub>DD</sub> ≤	≤ 5.5V	200			
Maximum Data Rate	DR <sub>MAX</sub>	1.71V ≤ V <sub>DD</sub> ≤		150			Mbps
	5,,,		$2.25V \le V_{DD} \le 5.5V$			5	
Minimum Pulse Width	PW <sub>MIN</sub>	I_ to O_	$1.71V \le V_{DD} \le 1.89V$		,	6.67	ns
			4.5V ≤ V <sub>DD</sub> ≤ 5.5V	4.1	5.4	9.2	
		I_ to O_,	3.0V ≤ V <sub>DD</sub> ≤ 3.6V	4.2	5.9	10.2	1
Propagation Delay (Figure 1)	t <sub>PLH</sub>	C <sub>L</sub> = 15pF	$2.25V \le V_{DD} \le 2.75V$	4.9	7.1	13.4	
			1.71V ≤ V <sub>DD</sub> ≤ 1.89V	7.1	10.9	20.3	1
			4.5V ≤ V <sub>DD</sub> ≤ 5.5V	4.3	5.6	9.4	ns
		I to O ,	3.0V ≤ V <sub>DD</sub> ≤ 3.6V	4.4	6.2	10.5	
	t <sub>PHL</sub>	C <sub>L</sub> = 15pF	2.25V ≤ V <sub>DD</sub> ≤ 2.75V	5.1	7.3	14.1	
		_	1.71V ≤ V <sub>DD</sub> ≤ 1.89V	7.2	10.9	21.7	1
Pulse Width Distortion	PWD	t <sub>PLH</sub> - t <sub>PHL</sub>			0.3	2	ns

# **Dynamic Characteristics (continued)**

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_L=15pF,~T_A=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_A=+25^{\circ}C,~unless~otherwise~noted.)~(Note~2)$ 

PARAMETER	SYMBOL	cc	ONDITIONS	MIN	TYP	MAX	UNITS	
		4.5V ≤ V <sub>DD</sub> ≤ 5.	5V			3.7		
		$3.0V \le V_{DD} \le 3.0$	6V			4.3		
	tSPLH	2.25V ≤ V <sub>DD</sub> ≤ 2			6			
Propagation Delay Skew		1.71V ≤ V <sub>DD</sub> _ ≤ 1	.89V			10.3		
Part-to-Part (Same Channel)		4.5V ≤ V <sub>DD</sub> _ ≤ 5.	5V			3.8	ns	
	t	$3.0V \le V_{DD} \le 3.0$	6V			4.7		
	tsphl	2.25V ≤ V <sub>DD</sub> _ ≤ 2	2.75V			6.5		
		1.71V ≤ V <sub>DD</sub> _ ≤ 1	.89V			11.5		
Propagation Delay Skew Channel-to-Channel	tscslh					2	200	
(Same Direction)	tscshl					2	ns	
		4.5V ≤ V <sub>DD</sub> ≤ 5.	5V			2.9		
	_	3.0V ≤ V <sub>DD</sub> ≤ 3.	6V			3.4		
	tscolh	2.25V ≤ V <sub>DD</sub> ≤ 2	2.75V			4.9		
Propagation Delay Skew Channel-to-Channel		1.71V ≤ V <sub>DD</sub> _ ≤ 1	.89V			10.2		
(Opposite Direction)		4.5V ≤ V <sub>DD</sub> ≤ 5.5V				3.2	ns	
	tscohl	$3.0V \le V_{DD} \le 3.0$	6V			3.8		
		2.25V ≤ V <sub>DD</sub> _ ≤ 2.75V				5.3		
		1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V				10.9		
Peak Eye Diagram Jitter	T <sub>JIT(PK)</sub>	200Mbps			250		ps	
Clock Jitter RMS	T <sub>JCK(RMS)</sub>	500kHz Clock Inp	out, Rising/Falling Edges		6.5		ps	
		$4.5V \le V_{DD} \le 5.5V$				1.6		
Rise Time	t <sub>R</sub>	$3.0V \le V_{DD} \le 3.6V$				2.2	ns	
Tibe Time	'K	$2.25 \text{V} \le \text{V}_{\text{DD}} \le 2.75 \text{V}$				3	ns	
		1.71V ≤ V <sub>DD</sub> _ ≤ 1	.89V			4.5		
		4.5V ≤ V <sub>DD</sub> _ ≤ 5.	5V			1.4		
Fall Time	t <sub>F</sub>	$3.0V \le V_{DD} \le 3.0$				2	ns	
		2.25V ≤ V <sub>DD</sub> _ ≤ 2				2.8	113	
		1.71V ≤ V <sub>DD</sub> _ ≤ 1				5.1		
		ICS or SDOEN	4.5V ≤ V <sub>DD</sub> _ ≤ 5.5V			31.3		
Enable to Data Valid	t <sub>EN</sub>	falling to OSDO	3.0V ≤ V <sub>DD</sub> _ ≤ 3.6V			34.8	ns	
		valid, C <sub>I</sub> = 15pF	2.25V ≤ V <sub>DD</sub> _ ≤ 2.75V			40.0	)	
			1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V			51.8		
		ICS or SDOEN	4.5V ≤ V <sub>DD</sub> _ ≤ 5.5V			33.9	ns	
Disable to Tri-state	<sup>t</sup> TRI tr	rising to OSDO $3.0V \le V_D$ tristate, $2.25V \le V$	3.0V ≤ V <sub>DD</sub> ≤ 3.6V			38.6		
			2.25V ≤ V <sub>DD</sub> ≤ 2.75V			44.4		
			1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V			55		

## **Dynamic Characteristics (continued)**

 $(V_{DDA} - V_{GNDA} = 1.71 \text{V to } 5.5 \text{V}, V_{DDB} - V_{GNDB} = 1.71 \text{V to } 5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted.}$  Typical values are at  $V_{DDA} - V_{GNDA} = 3.3 \text{V}, V_{DDB} - V_{GNDB} = 3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.}$  (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS			
CONTROL AND MONITOR CHANNELS - IRDY, SDOEN, SAA, SBA									
Common-Mode Transient Immunity	СМТІ	I_ = GND_ or V <sub>DD_</sub> (Note 4)		50		kV/μs			
Glitch Rejection		SDOEN	10	17	29	ns			
Propagation Delay	t <sub>PLH</sub>	IRDY low to high		100					
	t <sub>PHL</sub>	IRDY high to low		100		μs			
		$4.5V \le V_{DD} \le 5.5V$			1.6				
Rise Time	+_	$3.0V \le V_{DD} \le 3.6V$			2.2	ns			
Nise fillie	t <sub>R</sub>	$2.25V \le V_{DD_{-}} \le 2.75V$			3	115			
		1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V			4.5				
		4.5V ≤ V <sub>DD</sub> _ ≤ 5.5V			1.4				
Fall Time	t <sub>F</sub>	$3.0V \le V_{DD} \le 3.6V$		·	2	no			
		2.25V ≤ V <sub>DD</sub> _ ≤ 2.75V			2.8	ns			
		1.71V ≤ V <sub>DD</sub> _ ≤ 1.89V			5.1				

- Note 1: All devices are 100% production tested at  $T_A = +25$ °C. Specifications over temperature are guaranteed by design.
- Note 2: Not production tested. Guaranteed by design and characterization.
- **Note 3:** All currents into the device are positive. All currents out of the device are negative. All voltages are referenced to their respective ground (GNDA or GNDB), unless otherwise noted.
- **Note 4:** CMTI is the maximum sustainable common-mode voltage slew rate while maintaining the correct output. CMTI applies to both rising and falling common-mode voltage edges. Tested with the transient generator connected between GNDA and GNDB (V<sub>CM</sub> = 1000V).

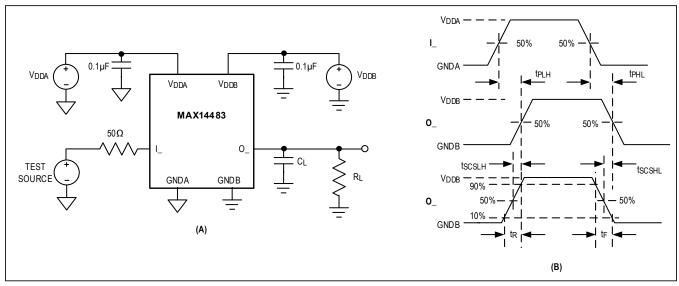


Figure 1. Test Circuit (A) and Timing Diagram (B)

### **ESD Protection**

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
ESD		Human Body Model, all pins		±4		kV

### **Insulation Characteristics**

## **Table 1. 20-pin SSOP Insulation Characteristics**

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS
Partial Discharge Test Voltage	V <sub>PR</sub>	Method B1 = V <sub>IORM</sub> x 1.875 (t = 1s, partial discharge < 5pC)	1050	V <sub>P</sub>
Maximum Repetitive Peak Isolation Voltage	V <sub>IORM</sub>	(Note 5)	560	$V_{P}$
Maximum Working Isolation Voltage	V <sub>IOWM</sub>	Continuous RMS voltage (Note 5)	400	$V_{RMS}$
Maximum Transient Isolation Voltage	V <sub>IOTM</sub>	t = 1s (Note 5)	5300	$V_{P}$
Maximum Withstand Isolation Voltage	V <sub>ISO</sub>	f <sub>SW</sub> = 60Hz, duration = 60s (Note 5, 6)	3750	$V_{RMS}$
Maximum Surge Isolation Voltage	V <sub>IOSM</sub>	Basic Insulation, 1.2/50µs pulse per IEC61000-4-5	10	kV
		V <sub>IO</sub> = 500V, T <sub>A</sub> = 25°C	>10 <sup>12</sup>	
Insulation Resistance	R <sub>IO</sub>	V <sub>IO</sub> = 500V, 100°C ≤ T <sub>A</sub> ≤ 125°C	>1011	Ω
		V <sub>IO</sub> = 500V, T <sub>S</sub> = 150°C	>10 <sup>9</sup>	
Barrier Capacitance Side A to Side B	CIO	f <sub>SW</sub> = 1MHz (Note 7)	1.5	pF
Minimum Creepage Distance	CPG	SSOP	5.5	mm
Minimum Clearance Distance	CLR	SSOP	5.5	mm
Internal Clearance		Distance through insulation	0.015	mm
Comparative Tracking Index	CTI	Material Group II (IEC 60112)	>400	
Climate Category			40/125/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	

Note 5:  $V_{ISO}$ ,  $V_{IOWM}$ ,  $V_{IOTM}$ , and  $V_{IORM}$  are defined by the IEC 60747-5-5 standard.

Note 6: Product is qualified at  $V_{ISO}$  for 60s and 100% production tested at 120% of  $V_{ISO}$  for 1s.

Note 7: Capacitance is measured with all pins on side A and side B tied together.

# **Safety Regulatory Approval**

#### UI

The MAX14483 is certified under UL1577. For more details, refer to File E351759.

Rated up to  $3750V_{\mbox{RMS}}$  isolation voltage for single protection.

#### **cUL (EQUIVALENT TO CSA NOTICE 5A)**

The MAX14483 is certified up to 3750V<sub>RMS</sub> for single protection. For more details, refer to File E351759.

### **Safety Limits**

Damage to the IC can result in a low-resistance path to ground or to the supply and, without current limiting, the MAX14483 could dissipate excessive amounts of power. Excessive power dissipation can damage the die and result in damage to the isolation barrier, potentially causing downstream issues. <u>Table 2</u> shows the safety limits for the MAX14483.

The maximum safety temperature  $(T_S)$  for the device is the 150°C maximum junction temperature specified in the <u>Absolute Maximum Ratings</u>. The power dissipation  $(P_D)$  and junction-to-ambient thermal

impedance  $(\theta_{JA})$  determine the junction temperature. Thermal impedance values  $(\theta_{JA})$  and  $\theta_{JC}$  are available in the <u>Package Information</u> section and power dissipation calculations are discussed in the <u>Calculating Power Dissipation</u> section. Calculate the junction temperature  $(T_J)$  as:

$$T_J = T_A + (P_D \times \theta_{JA})$$

<u>Figure 2</u> and <u>Figure 3</u> show the thermal derating curve for safety limiting the power and the current of the device. Ensure that the junction temperature does not exceed 150°C.

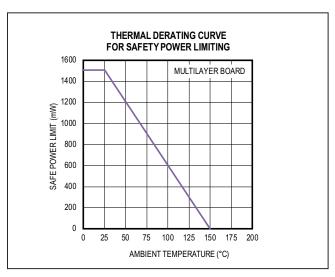


Figure 2. Thermal Derating Curve for Safety Power Limiting

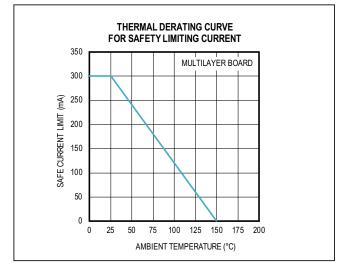


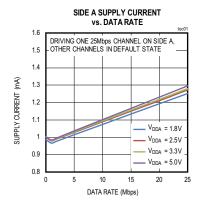
Figure 3. Thermal Derating Curve for Safety Current Limiting

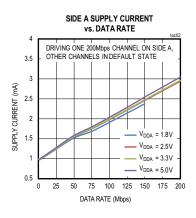
# **Table 2. Safety Limiting Values for the MAX14483**

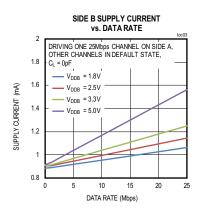
PARAMETER	SYMBOL	TEST CONDITIONS	MAX	UNIT
Safety Current on Any Pin (No Damage to Isolation Barrier)	IS	T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, Multilayer Board	300	mA
Total Safety Power Dissipation	PS	T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, Multilayer Board	1506	mW
Maximum Safety Temperature	T <sub>S</sub>		150	°C

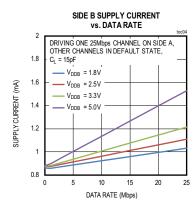
## **Typical Operating Characteristics**

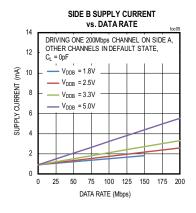
 $(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25$ °C, unless otherwise noted.)

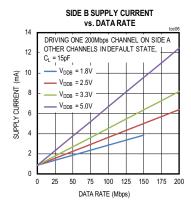


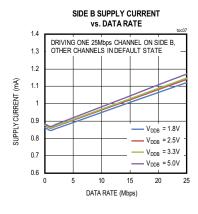




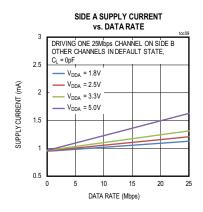






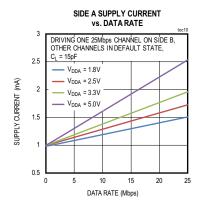


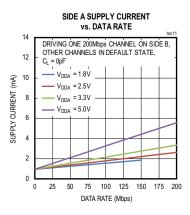


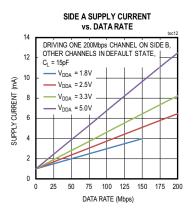


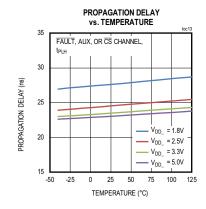
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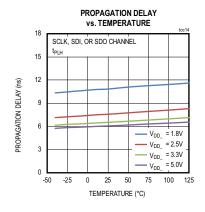
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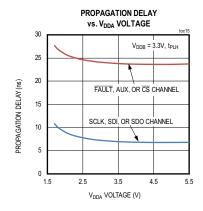


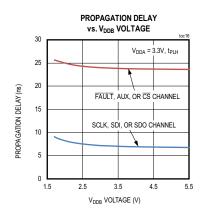






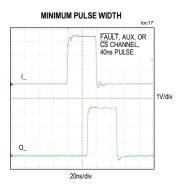


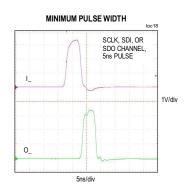


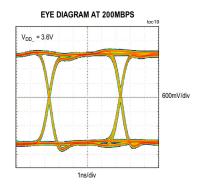


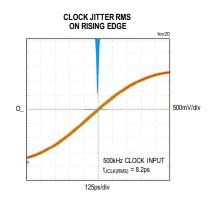
# **Typical Operating Characteristics (continued)**

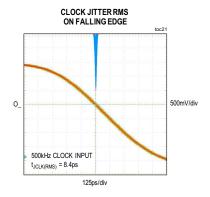
 $(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25$ °C, unless otherwise noted.)

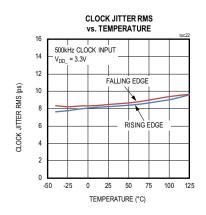




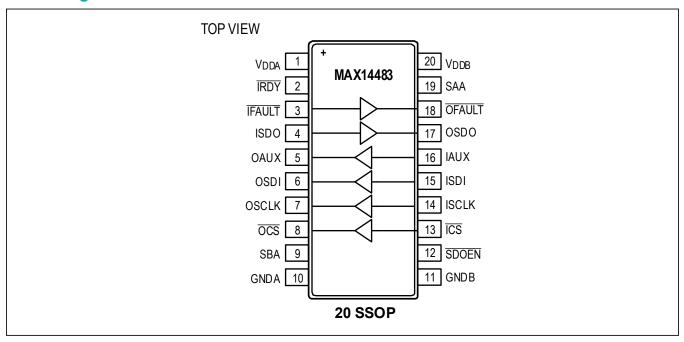








# **Pin Configurations**



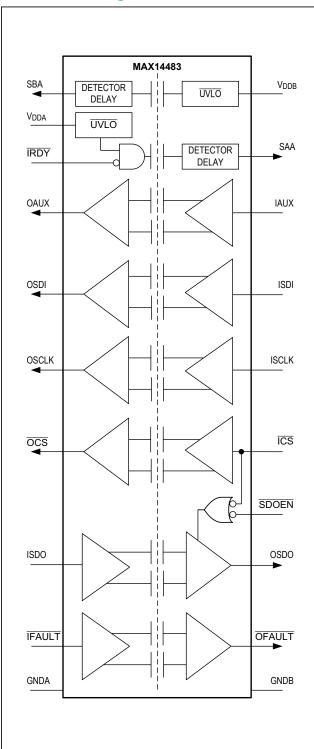
# **Pin Description**

PIN	NAME	FUNCTION	REFERENCE
SIDE A (S	SPI SLAVE)		
1	V <sub>DDA</sub>	Power Supply. Bypass $V_{\text{DDA}}$ with a $0.1\mu\text{F}$ ceramic capacitor as close as possible to the pin.	GNDA
2	ĪRDY	Ready Input. Assert IRDY low when Side A is ready for communication. When IRDY is high, SAA is low and Side B outputs are in their default state (OFAULT is low and OSDO is low when enabled). When IRDY is low, and Side A power is valid, SAA is high and Side B outputs operate normally. If the ready function is not required, tie IRDY to GNDA.	GNDA
3	IFAULT	Input to FAULT channel; has a weak internal pulldown.	GNDA
4	ISDO	Input to SDO channel; has a weak internal pulldown. Connect to MISO of slave device(s).	GNDA
5	OAUX	Output of AUX channel.	GNDA
6	OSDI	Output of SDI channel. Connect to MOSI of slave device(s).	GNDA
7	OSCLK	Output of SCLK channel. Connect to SCLK of slave device(s).	GNDA
8	OCS	Output of $\overline{CS}$ channel. Connect to $\overline{CS}$ of slave device(s).	GNDA

# **Pin Description (continued)**

PIN	NAME	FUNCTION	REFERENCE
9	SBA	Side B Active. SBA is high when Side B has power and is operating normally. When Side B is not powered, SBA is set low and all Side A outputs are in their default state. A nominal 100µs delay is added between the detection of Side B power and the assertion of SBA. This allows time for the power supply to settle, and ensures a minimum low pulse width for SBA.	GNDA
10	GNDA	Power and Signal Ground for Side A	GNDA
SIDE B (	SPI MASTER)		
20	V <sub>DDB</sub>	Power Supply. Bypass $V_{\mbox{\scriptsize DDB}}$ with a 0.1 $\mu \mbox{\scriptsize F}$ ceramic capacitor as close as possible to the pin.	GNDB
19	SAA	Side A Active. SAA is high when Side A has power, is operating normally, and \$\overline{IRDY}\$ is low. When Side A is not powered, SAA is set low and all Side B outputs are in their default state (\$\overline{OFAULT}\$ is low and OSDO is low when enabled). A nominal 100µs delay is added between the detection of Side A power and the assertion of SAA. This allows time for the power supply to settle, and ensures a minimum low pulse width for SAA.	GNDB
18	OFAULT	Output of FAULT channel. Open Drain Output	GNDB
17	OSDO	Output of SDO channel. Tri-stated when $\overline{\text{ICS}}$ and $\overline{\text{SDOEN}}$ are both high. Connect to MISO of SPI master.	GNDB
16	IAUX	Input to AUX channel; has a weak internal pullup to V <sub>DDB</sub>	GNDB
15	ISDI	Input to SDI channel; has a weak internal pulldown. Connect to MOSI of SPI master.	GNDB
14	ISCLK	Input to SCLK channel; has a weak internal pulldown. Connect to SCLK of SPI master.	GNDB
13	īCS	Input to $\overline{\text{CS}}$ channel; has a weak internal pullup to V <sub>DDB</sub> . Connect to $\overline{\text{CS}}$ output or GPO of SPI master. When $\overline{\text{ICS}}$ is low, OSDO output is enabled.	
12	SDOEN	SDO Enable; has a weak internal pullup to V <sub>DDB</sub> . When SDOEN is low, the OSDO output is enabled, allowing the SDO channel to be used with multiple side A SPI slaves.	GNDB
11	GNDB	Power and Signal Ground for Side B	GNDB

# **Functional Diagram**



### **Detailed Description**

The MAX14483 is a 6-channel, 3.75kV<sub>RMS</sub> digital galvanic isolator using Maxim's proprietary process technology. The six signal channels are individually optimized for SPI applications and include very low propagation delay on the SDI, SDO, and SCLK channels. The SDO channel's tri-state control is enabled by the CS input as well as a second enable control input pin (SDOEN), allowing a single MAX14483 to isolate multiple SPI devices. To simplify system design, an open drain FAULT output can be wire ORed with error outputs from other devices. In addition, an auxiliary channel (AUX) is available for passing timing or control signals from the master side to the slave side and power monitors (SAA, SBA) are provided for both power domains to signal that the opposite side of the isolator is ready for operation. Independent 1.71V to 5.5V supplies on each side of the isolator also make the device suitable for use as a level translator.

The MAX14483 offers low-power operation, high electromagnetic interference (EMI) immunity, and stable temperature performance through Maxim's proprietary process technology. The device isolates different ground domains and blocks high-voltage/high-current transients from sensitive or human interface circuitry.

The MAX14483 is available with a maximum data rate of 200Mbps (SPI Data Rate Channels). The device has two supply inputs ( $V_{DDA}$  and  $V_{DDB}$ ) that independently set the logic levels on either side of device.  $V_{DDA}$  and  $V_{DDB}$  are referenced to GNDA and GNDB, respectively.

The MAX14483 also features an internal refresh circuit to ensure output accuracy when an input remains in the same state indefinitely.

#### **Digital Isolation**

The MAX14483 provides galvanic isolation for digital signals that are transmitted between two ground domains. The device withstands up to 560V<sub>PEAK</sub> of continuous isolation and up to 3.75kV<sub>RMS</sub> for up to 60 seconds in the 20-pin SSOP package, which has 5.5mm of creepage and clearance. The package material has a minimum comparative tracking index (CTI) of 400V, giving it a group 2 rating in creepage tables.

#### Level-Shifting

The wide supply voltage range of both  $V_{DDA}$  and  $V_{DDB}$  allows the MAX14483 to be used for level translation in addition to isolation.  $V_{DDA}$  and  $V_{DDB}$  can be independently set to any voltage from 1.71V to 5.5V. The supply voltage sets the logic level on the corresponding side of the isolator.

#### **Isolation Channels**

The MAX14483 has three types of channels (Table 3). Low Data Rate Channels are FAULT, AUX and CS. SPI Data Rate Channels are SCLK, SDI, and SDO. Control and Monitor Channels are IRDY, SDOEN, SAA and SBA. Different types of channels have different electrical specifications.

#### Low Data Rate Channels

The Low Data Rate Channels are FAULT, AUX, and  $\overline{\text{CS}}$ . Each channel is unidirectional; it only passes data in one direction, as indicated in the functional diagram. Each channel has a maximum data rate of 25Mbps. The FAULT and AUX channels are designed to support SPI devices which require control signals beyond the standard 4-wire SPI bus. The output drivers of AUX and  $\overline{\text{CS}}$  channels are push-pull, eliminating the need for pullup resistors. The FAULT channel output is open drain and requires a pullup resistor. All the outputs are able to drive both TTL and CMOS logic inputs. The input channels have an integrated glitch filter to help operate in noisy environments and avoid false triggering.

#### **SPI Data Rate Channels**

The SPI Data Rate Channels are SCLK, SDI, and SDO; these channels are designed to support standard 4-wire SPI bus signals ( $\overline{\text{CS}}$  is considered as a Low Data Rate Channel). Each channel is unidirectional; it only passes

data in one direction, as indicated in the functional diagram. Each channel has been optimized for fast data rate and minimal skew between channels, with a maximum data rate of 200Mbps and maximum channel-to-channel propagation delay skew of only 10.2ns with  $V_{DD}$  = 1.8V. The output driver of each channel is push-pull, eliminating the need for pullup resistors. The outputs are able to drive both TTL and CMOS logic inputs.

#### **Control and Monitor Channels**

The Control and Monitor Channels are IRDY, SDOEN, SAA and SBA. Each channel is unidirectional; it only passes data in one direction, as indicated in the functional diagram. The monitor channels (SAA, SBA) are designed to pass essentially DC signals and have significantly longer propagation delays than other channels, meaning they should not be used for data signals. The outputs are able to drive both TTL and CMOS logic inputs. SAA and SBA are set high when their respective opposite side of the isolator has power and is operating normally. When Side A or Side B is not powered, SAA or SBA is set low and all outputs are set to their default state (OSDO is high impedance when disabled). A nominal 100µs delay is added between the detection of the opposite side power and the assertion of SAA or SBA. This allows time for the power supply to settle, and ensures a minimum low pulse width for SAA and SBA.

**Table 3. Channel Summary** 

CHANNEL TYPE	CHANNEL	OUTPUT DEFAULT	INPUT CURRENT SOURCE	GLITCH FILTER
Low Data Rate	FAULT	Low	Pull Down	Yes
Low Data Rate	AUX	High	Pull Up	Yes
Low Data Rate	CS	High	Pull Up	Yes
SPI Data Rate	SDI	Low	Pull Down	No
SPI Data Rate	SCLK	Low	Pull Down	No
SPI Data Rate	SDO	Low	Pull Down	No
Control and Monitor	SDOEN	Input Only	Pull Up	Yes
Control and Monitor	ĪRDY	Input Only	Pull Up	Yes
Control and Monitor	SAA	High when Side A has power, is operating normally, and $\overline{\text{IRDY}}$ is low. Low when Side A is not powered or $\overline{\text{IRDY}}$ is high.	N/A	N/A
Control and Monitor	and Monitor SBA High when Side B has power and is operating normally.  Low when Side B is not powered.		N/A	N/A

The control channels (IRDY, SDOEN) have an integrated glitch filter. IRDY is an external input from the A side circuits (such as a Digital I/O device) to indicate that these devices are powered and active, allowing the B side circuit (such as a MCU SPI Master) to initiate data transfer across the isolation barrier. SDOEN is an output enable control for OSDO. SDOEN allows the B side of the MAX14483 to be shared with multiple SPI devices on the A side by enabling OSDO when ICS is not asserted. The A side SPI devices can be configured either in the daisy chain mode, where a single CS signal enables all Side A devices as well as the OSDO output, or in the independent slave mode, where one Side A device uses the CS channel in the MAX14483 and the rest of the Side A devices have their own  $\overline{CS}$  isolator channels, external to the MAX14483. The independent slave mode requires OSDO to be enabled any time one of the  $\overline{\text{CS}}$  signals is asserted, which can be accomplished by connecting a GPO pin to SDOEN and asserting it any time any CS signal is asserted. In the case that the B side of the MAX14483 is not shared with multiple SPI devices, there is no need for OSDO to be high impedance, and SDOEN can be permanently connected to GNDB. Refer to Typical Operating Circuits for details.

### Startup and Undervoltage-Lockout

The V<sub>DDA</sub> and V<sub>DDB</sub> supplies are both internally monitored for undervoltage conditions. Undervoltage events can occur during power-up, power-down, or during normal operation due to a sagging supply voltage. When an undervoltage condition is detected on either supply, all outputs go to their default states regardless of the state of the inputs (Table 4). Figure 4 through Figure 6 show the behavior of the SAA and SBA signals during power-up, power-down and  $\overline{\text{IRDY}}$  toggling.

## **Applications Information**

### **Power-Supply Sequencing**

The MAX14483 does not require special power supply sequencing. The logic levels are set independently on either side by  $V_{DDA}$  and  $V_{DDB}$ . Each supply can be present over the entire specified range regardless of the level or presence of the other supply.

### **Power-Supply Decoupling**

To reduce ripple and the chance of introducing data errors, bypass  $V_{DDA}$  and  $V_{DDB}$  with  $0.1\mu F$  low-ESR ceramic capacitors to GNDA and GNDB, respectively. Place the bypass capacitors as close to the power supply input pins as possible.

Table 4. Output B	ehavior During	Undervoltage (	Conditions
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V <sub>IN</sub> _	V	V <sub>DDB</sub>	V <sub>OUTA</sub>	SDO ENABLE*	V <sub>OUTB</sub>	
I_	$V_{DDA}$		0_		OSDO	OFAULT
1	Powered	Powered -	1	0	Hi-Z	1
'			1	1	1	1
0	Powered	Powered	0	0	Hi-Z	0
0			0	1	0	0
X	l la dominita do	Powered	Default	0	Hi-Z	Default
^	Undervoltage		Default	1	Default	Default
X	Powered	Undervoltage -	Default	0	Hi-Z	Default
^			Default	1	Default	Default

<sup>\*</sup> The SDO channel is enabled by either ICS or SDOEN being low. See Table 5 for details.

### Table 5. ICS, SDOEN, and OSDO Truth Table

ĪCS	SDOEN	OSDO
0	0	Enabled; OSDO follows ISDO;
0	1	Enabled; OSDO follows ISDO;
1	0	Enabled; OSDO follows ISDO;
1	1	High-Impedance

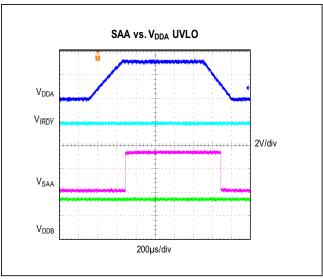


Figure 4. VDDA - UVLO Controlling SAA Signal

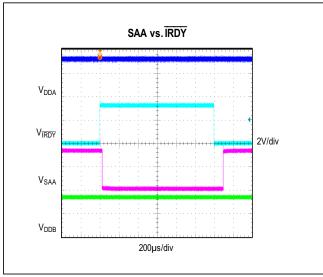


Figure 5. IRDY Controlling SAA Signal

### **Layout Considerations**

The PCB designer should follow some critical recommendations in order to get the best performance from the design.

- Keep the input/output traces as short as possible.
   Avoid using vias to make low-inductance paths for the signals.
- Have a solid ground plane underneath the highspeed signal layer.

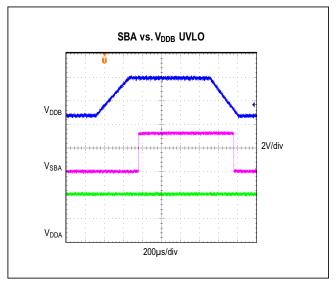


Figure 6. VDDB - UVLO Controlling SBA Signal

 Keep the area underneath the MAX14483 free from ground and signal planes. Any galvanic or metallic connection between the Side A and the Side B defeats the isolation.

### **Calculating Power Dissipation**

The required current for a given supply ( $V_{DDA}$  or  $V_{DDB}$ ) can be estimated by summing the current required for each channel. The supply current for a channel depends on whether the channel is an input or an output, the channel's data rate, and the capacitive or resistive load if it is an output. The typical current for an input or output at any data rate can be estimated from the graphs in <u>Figure 7</u> and <u>Figure 8</u>. Please note the data in <u>Figure 7</u> and <u>Figure 8</u> are extrapolated from the supply current measurements in a typical operating condition.

The total current for a single channel is the sum of the "no load" current (shown in <u>Figure 7</u> and <u>Figure 8</u>), which is a function of Voltage and Data Rate, and the "load current", which depends on the type of load. Current into a capacitive load is a function of the load capacitance, the switching frequency, and the supply voltage.

$$I_{Cl} = C_{l} \times f_{SW} \times V_{DD}$$

where

 $I_{CL}$  is the current required to drive the capacitive load.  $C_L$  is the load capacitance on the isolator's output pin.  $f_{SW}$  is the switching frequency (bits per second / 2).  $V_{DD}$  is the supply voltage on the output side of the isolator.

Current into a resistive load depends on the resistance, the supply voltage and the average duty cycle of the data waveform. The DC load current can be conservatively estimated by assuming the output is always high.

$$I_{RI} = V_{DD} \div R_{I}$$

where

I<sub>RI</sub> is the current required to drive the resistive load.

V<sub>DD</sub> is the supply voltage on the output side of the isolator.

R<sub>I</sub> is the load resistance on the isolator's output pin.

In the case of an SPI bus which often has intermittent read or write cycles, one other factor to consider is the active duty cycle percentage as well as the typical active current.

Example (shown in Figure 9): An SPI Master running at 10MHz and with 8-bit data package. The MAX14483 is operating with V<sub>DDB</sub> = 2.5V, V<sub>DDA</sub>= 3.3V, SCLK operating at 20Mbps with a 15pF load, SDI and SDO channels operating in 8-bit data frame at 10Mbps with a 15pF load on each,  $\overline{\text{CS}}$  operating at effective rate of 2.5Mbps (20Mbps divide by 8) with a 15pF load, and AUX channel operating at 1Mbps with a 10pF load. Channels SAA and SBA are not in use and FAULT drives a resistive load when active. Refer to Table 6 and Table 7 for V<sub>DDA</sub> and V<sub>DDB</sub> supply current calculation worksheets.

#### **V<sub>DDA</sub>** must supply:

- ISDO operating at 3.3V and 10Mbps, consuming 0.24mA, estimated from Figure 7.
- IFAULT operating at 3.3V and DC, consuming 0.14mA, estimated from Figure 7.

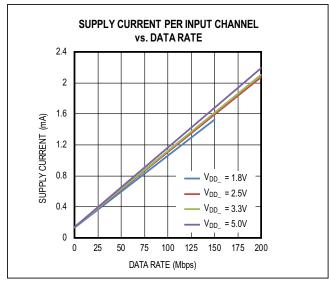


Figure 7. Supply Current Per Input Channel

- OAUX operating at 3.3V and 1Mbps, consuming 0.19mA, estimated from Figure 8. ICL on OAUX for 10pF capacitor at 3.3V is 0.017mA.
- OSDI operating at 3.3V and 10Mbps, consuming 0.30mA, estimated from Figure 8. ICL on OSDI for 15pF capacitor at 3.3V is 0.25mA.
- OSCLK operating at 3.3V and 20Mbps, consuming 0.42mA, estimated from Figure 8. I<sub>CI</sub> on OSCLK for 15pF capacitor at 3.3V is 0.50mA.
- OCS operating at 3.3V and 2.5Mbps, consuming 0.21mA, estimated from Figure 8. I<sub>CL</sub> on OCS for 15pF capacitor at 3.3V is 0.062mA.

## Total current for side A = 2.33mA, typical.

### **V<sub>DDB</sub>** must supply:

- IAUX operating at 2.5V and 1Mbps, consuming 0.15mA, estimated from Figure 7.
- ISDI operating at 2.5V and 10Mbps, consuming 0.23mA, estimated from Figure 7.
- ISCLK operating at 2.5V and 20Mbps, consuming 0.33mA, estimated from Figure 7.
- ICS operating at 2.5V and 2.5Mbps, consuming 0.16mA, estimated from Figure 7.
- OSDO operating at 2.5V and 10Mbps, consuming 0.27mA, estimated from Figure 8. ICL on OSDO for 15pF capacitor at 2.5V is 0.19mA.
- OFAULT operating at 2.5V and 1Mbps, consuming 0.18mA, estimated from Figure 8. IRI on OFAULT for  $10k\Omega$  resistor at 2.5V is 0.25mA.

Total current for side B = 1.76mA, typical.

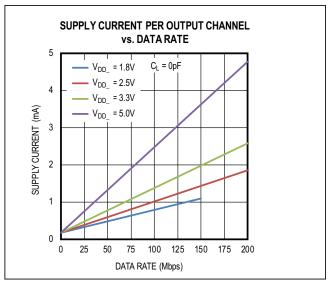


Figure 8. Supply Current Per Output Channel

**Table 6. Side A Supply Current Calculation Worksheet** 

SIDE A	V <sub>DDA</sub> = 3.3V					
Channel	IN/OUT	Data Rate (Mbps)	Load Type	Load	"No Load" Current (mA)	Load Current (mA)
OAUX	OUT	1	Capacitive	10pF	0.19	3.3V × 0.5MHz × 10pF = 0.017
OSDI	OUT	10	Capacitive	15pF	0.30	3.3V × 5MHz × 15pF = 0.25
OSCLK	OUT	20	Capacitive	15pF	0.42	3.3V × 10MHz × 15pF = 0.50
OCS	OUT	2.5	Capacitive	15pF	0.21	3.3V × 1.25MHz × 15pF = 0.062
ISDO	IN	10			0.24	
IFAULT	IN	0			0.14	
Total: 2.33mA						

**Table 7. Side B Supply Current Calculation Worksheet** 

SIDE B	V <sub>DDB</sub> = 2.5V						
Channel	IN/OUT	Data Rate (Mbps)	Load Type	Load	"No Load" Current (mA)	Load Current (mA)	
IAUX	IN	1			0.15		
ISDI	IN	10			0.23		
ISCLK	IN	20			0.33		
ĪCS	IN	2.5			0.16		
OSDO	OUT	10	Capacitive	15pF	0.27	2.5V × 5MHz × 15pF = 0.19	
OFAULT	OUT	0	Resistive	10kΩ	0.18	2.5V ÷ 10kΩ = 0.25	
	Total: 1.76mA						

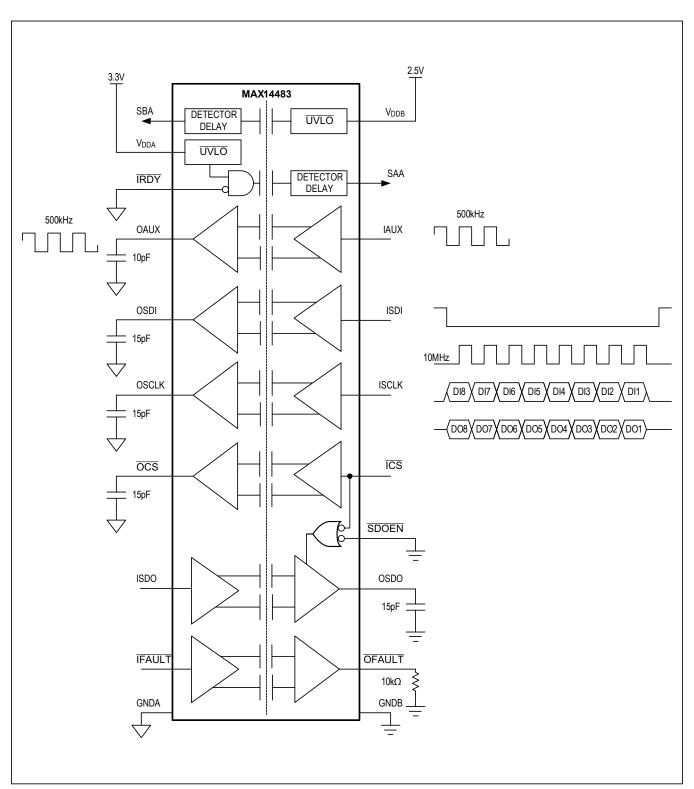
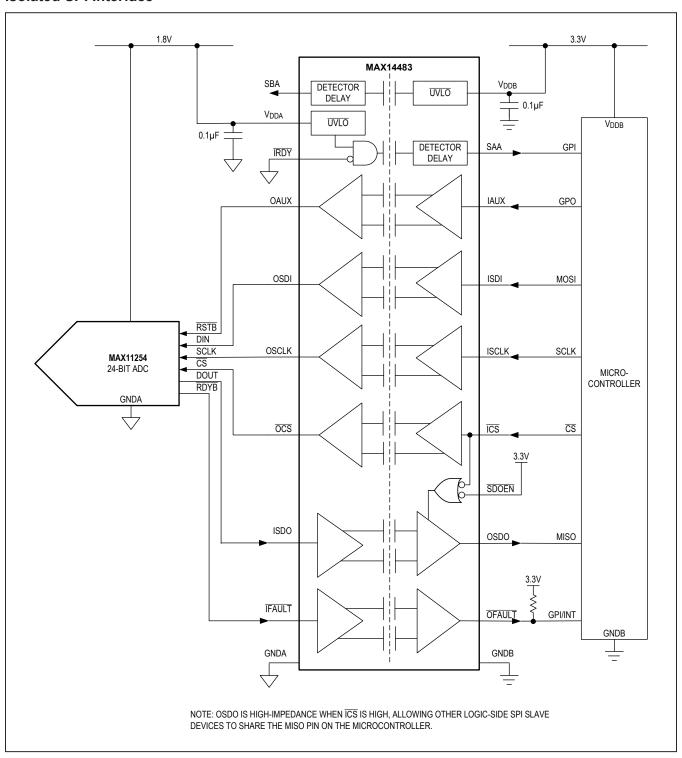


Figure 9. Example Circuit for Supply Current Calculation

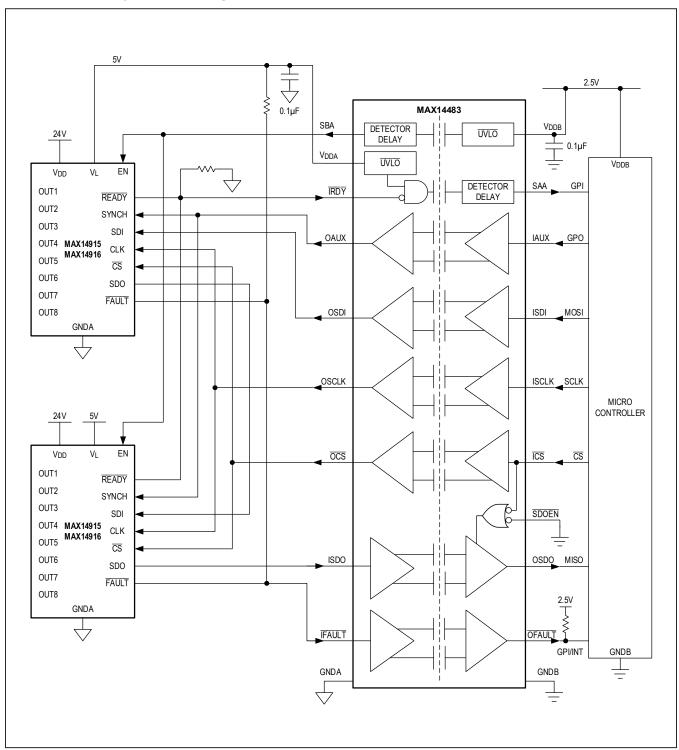
# **Typical Operating Circuit**

## Isolated SPI Interface



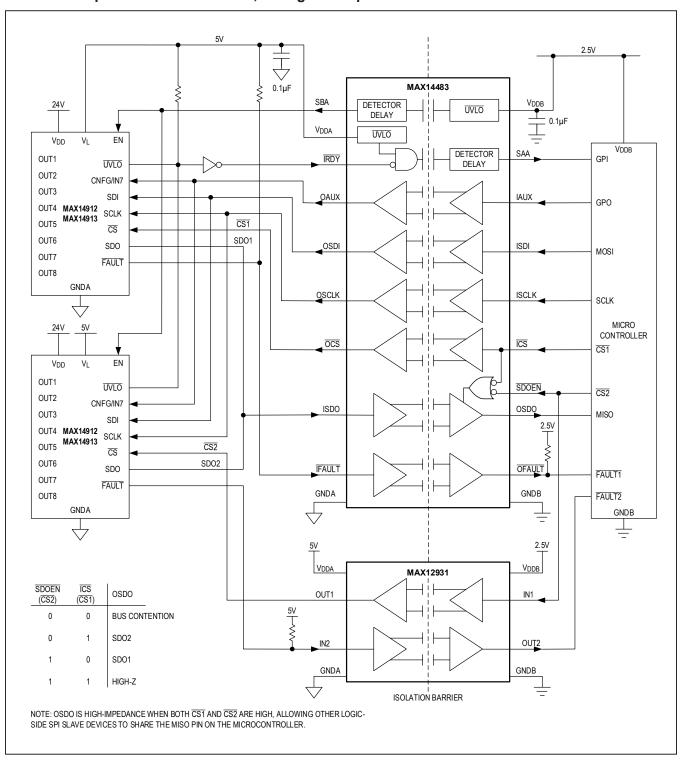
# **Typical Operating Circuit (continued)**

Isolated SPI Daisy Chain, 16 Digital Outputs



# **Typical Operating Circuit (continued)**

### Isolated Independent Slave SPI Bus, 16 Digital Outputs



MAX14483

6-Channel, Low-Power, 3.75kV<sub>RMS</sub>, SPI Digital Isolator

# **Ordering Information**

PART	ISOLATION VOLTAGE (KVRMS)	TEMP RANGE (°C)	PIN-PACKAGE
MAX14483AAP+	3.75	-40 to +125	20-SSOP

# **Chip Information**

PROCESS: BiCMOS